a gate electrode in said trench; and

a gate electrode insulating region lining the first and second sidewalls of said trench, said gate electrode insulating region having a first thickness less than about 750 Å as measured between said gate electrode and a first intersection between the first sidewall and the first P-N junction and a second thickness greater than about 1500 Å as measured between said gate electrode and a second intersection between the first sidewall and the second P-N junction.

42. The device of claim **41**, further comprising a Schottky contact adjacent the first face, said Schottky contact forming a Schottky rectifying junction with a portion of said drift region extending opposite the second sidewall of said trench.

43. The device of claim **42**, wherein said drift region has a graded first conductivity type doping concentration therein which decreases in a direction from said drain region to said base region.

44. The device of claim **43**, wherein said drift region includes a uniformly doped region of first conductivity type therein extending adjacent the first face; and wherein said Schottky contact forms a Schottky rectifying junction with said uniformly doped region.

45. The device of claim **44**, wherein a bottom of said trench defines an interface between said gate electrode insulating region and said drain region.

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